

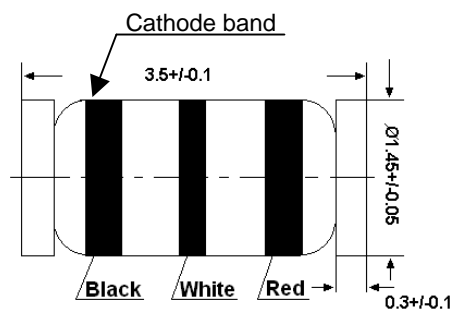
SILICON EPITAXIAL PLANAR DIODE

LL-34

fast switching diode in MiniMELF case especially suited for automatic surface mounting.

These diodes are delivered taped.

Details see "Taping".



Glass case MiniMELF
Dimensions in mm

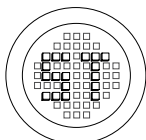
Absolute Maximum Ratings ($T_a = 25^{\circ}\text{C}$)

| | Symbol | Value | Unit |
|--|-----------|-------------|--------------------|
| Reverse Voltage | V_R | 220 | V |
| Peak Reverse Voltage | V_{RM} | 250 | V |
| Mean Rectified Current Half Wave Rectification with Resistance load at $T_{amb} = 25^{\circ}\text{C}$ and $f/50\text{ Hz}$ | I_O | 200 | mA |
| Maximum Forward Current | I_{FSM} | 625 | mA |
| Surge Forward Current at $t < 1\text{s}$ and $T_j = 25^{\circ}\text{C}$ | I_{FSM} | 1000 | mA |
| Junction Temperature | T_j | 175 | $^{\circ}\text{C}$ |
| Storage Temperature Range | T_S | -65 to +175 | $^{\circ}\text{C}$ |

¹⁾ Valid provided that electrodes are kept at ambient temperature.

Characteristics at $T_j = 25^{\circ}\text{C}$

| | Symbol | Min. | Typ. | Max. | Unit |
|--|-----------|------|------|------|---------------|
| Forward Voltage at $I_F = 200\text{mA}$ | V_F | - | - | 1.5 | V |
| Leakage Current at $V_R = 220\text{V}$ | I_R | - | - | 10 | μA |
| Reverse Breakdown Voltage tested with $100\mu\text{A}$ Pulses | V_{BR} | 250 | - | - | V |
| Capacitance at $V_F = V_R = 0, f = 1\text{MHz}$ | C_{tot} | - | - | 3 | pF |
| Reverse Recovery Time from $I_F = I_R = 20\text{mA}$ | t_{rr} | - | - | 75 | ns |



®

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